



ABSTRACT

METHODS AND LAYERS FOR METALLIZATION

One aspect of the present invention is a method of making an electronic device. According to one embodiment, the method comprises depositing a cap layer containing at least one dopant onto a gapfill metal and annealing so that the at least one dopant migrates to grain boundaries and/or interfaces of the gapfill metal. Another aspect of the present invention is an electronic device.

Fig. 1